# MAGNETORESISTANCE EFFECT DEVICE

## ABSTRACT OF THE DISCLOSURE

A magnetoresistance effect device has a fixed ferromagnetism layer, a free ferromagnetism layer, and a barrier layer sandwiched by these ferromagnetic layers. it is constituted so that CoFeB whose amount of addition of boron B (b: atomic %) is $21\% \leqq b \leqq 23\%$ may be used for the free ferromagnetism layer. In the magnetic resistance effect element, a magnetostrictive constant does not change steeply near the magnetostrictive constant zero. A MR ratio is maintained to be high.

Figure 1